

**Features**

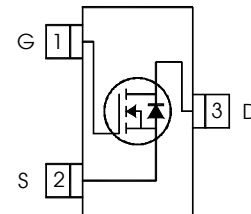
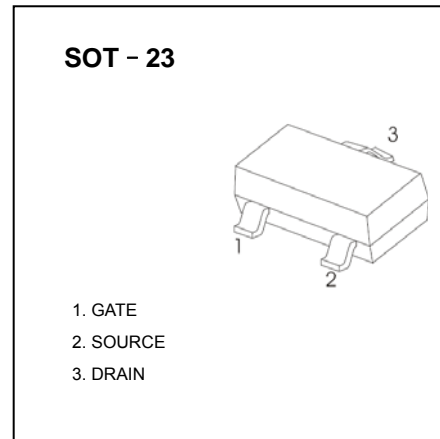
- $V_{DS(V)} = 30V$
- $R_{DS(ON)} < 100m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 154m\Omega$  ( $V_{GS} = 4.5V$ )

**Application(s)**

- Load/ System Switch

**Benefits**

- Multi-vendor compatibility
- Easier manufacturing RoHS
- Environmentally friendly
- Increased reliability



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.7	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.2	
$I_{DM}$	Pulsed Drain Current	11	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient <sup>③</sup>	—	100	°C/W
$R_{\theta JA}$	Junction-to-Ambient (t<10s) <sup>④</sup>	—	99	

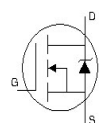
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on 1 in square Cu board

### Electric Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	80	100	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.7A ②
		—	123	154		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.2A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.3	1.7	2.3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 25μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
R <sub>G</sub>	Internal Gate Resistance	—	7.6	—	Ω	
g <sub>fs</sub>	Forward Transconductance	2.6	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.7A
Q <sub>g</sub>	Total Gate Charge	—	1.0	—	nC	I <sub>D</sub> = 2.7A
Q <sub>gs</sub>	Gate-to-Source Charge	—	0.34	—		V <sub>DS</sub> = 15V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	0.34	—		V <sub>GS</sub> = 4.5V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	4.1	—	ns	V <sub>DD</sub> = 15V ②
t <sub>r</sub>	Rise Time	—	3.3	—		I <sub>D</sub> = 1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	4.5	—		R <sub>G</sub> = 6.8Ω
t <sub>f</sub>	Fall Time	—	2.9	—		V <sub>GS</sub> = 4.5V
C <sub>iss</sub>	Input Capacitance	—	110	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	29	—		V <sub>DS</sub> = 15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	12	—		f = 1.0MHz

### Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	1.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	11		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 2.7A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	9.0	14	ns	T <sub>J</sub> = 25°C, V <sub>R</sub> = 15V, I <sub>F</sub> = 2.7A
Q <sub>rr</sub>	Reverse Recovery Charge	—	0.3	0.4	nC	di/dt = 100A/μs ②

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

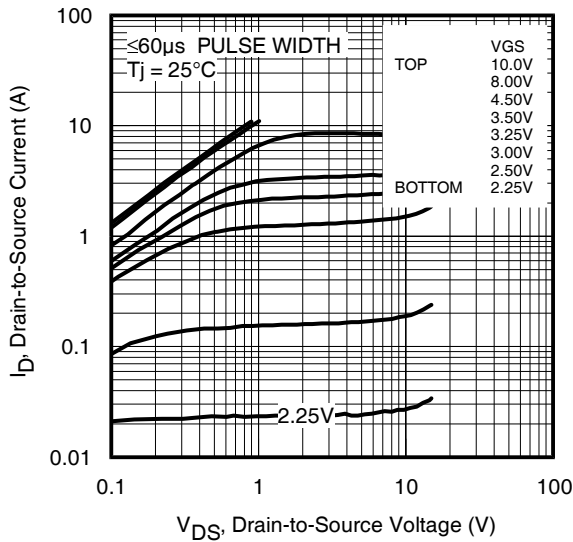


Fig 1. Typical Output Characteristics

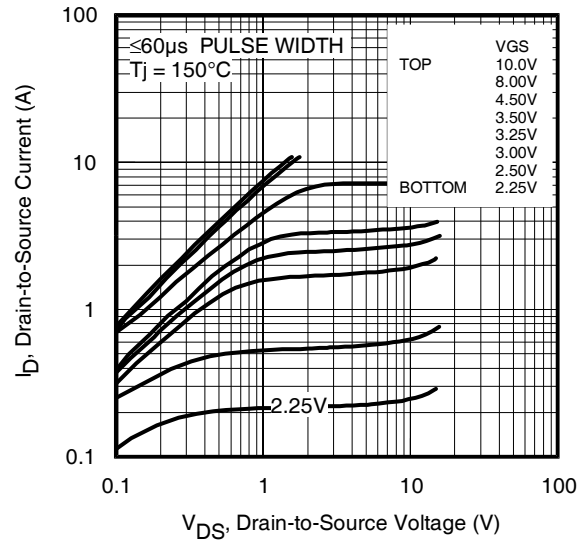


Fig 2. Typical Output Characteristics

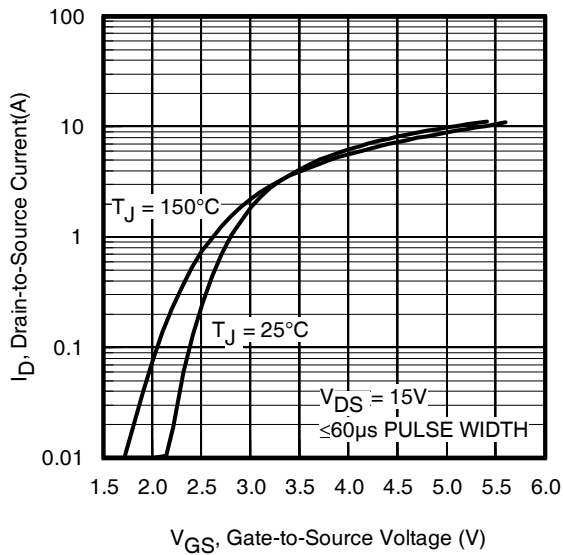


Fig 3. Typical Transfer Characteristics

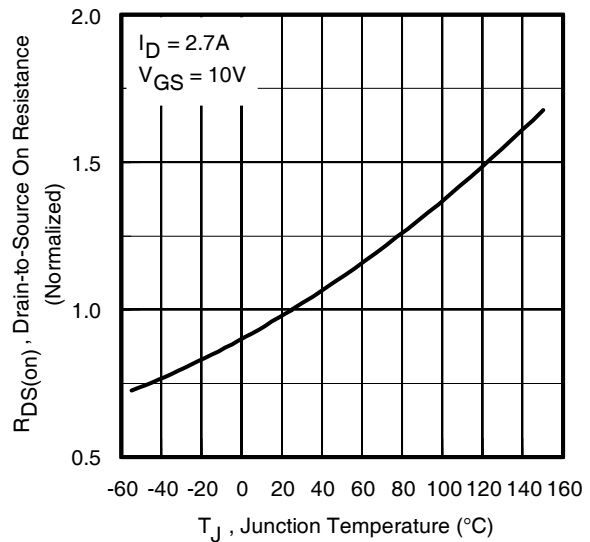


Fig 4. Normalized On-Resistance Vs. Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

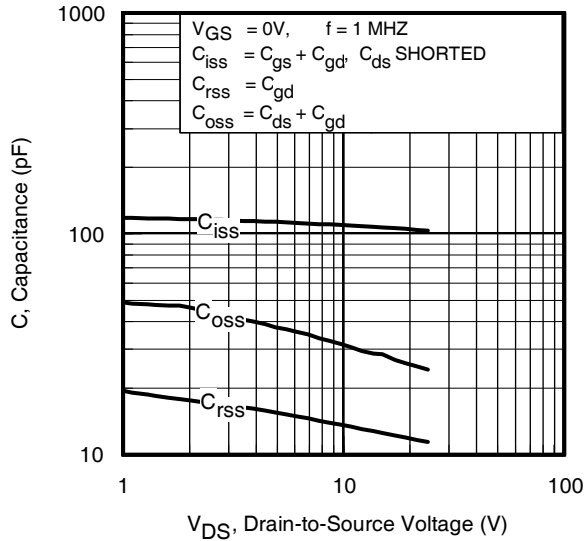


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

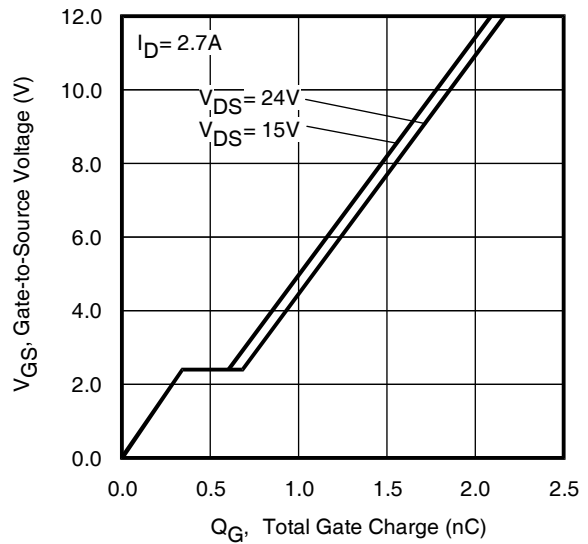


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

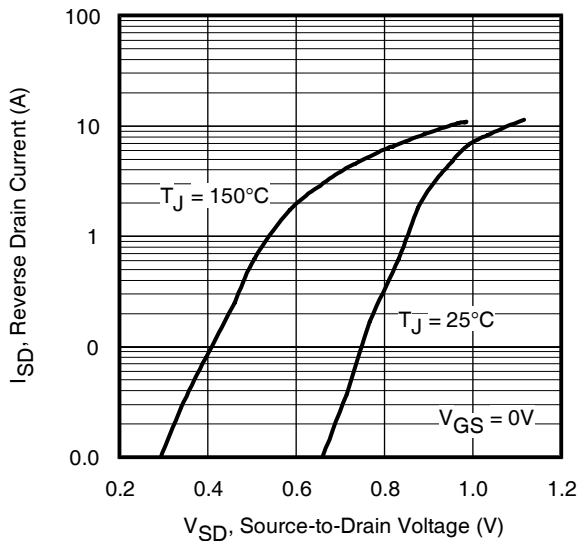


Fig 7. Typical Source-Drain Diode Forward Voltage

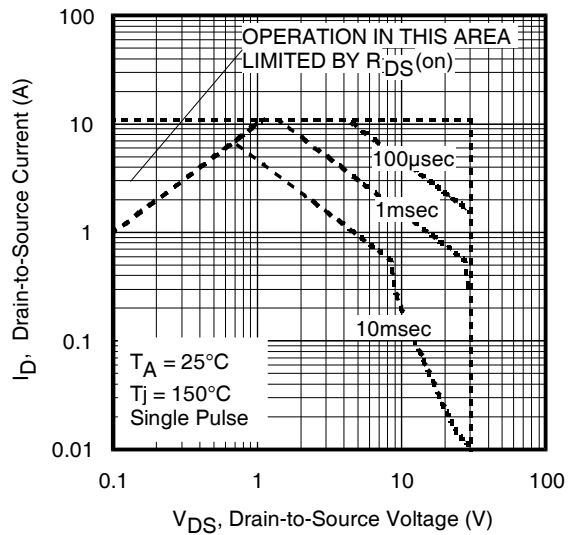


Fig 8. Maximum Safe Operating Area

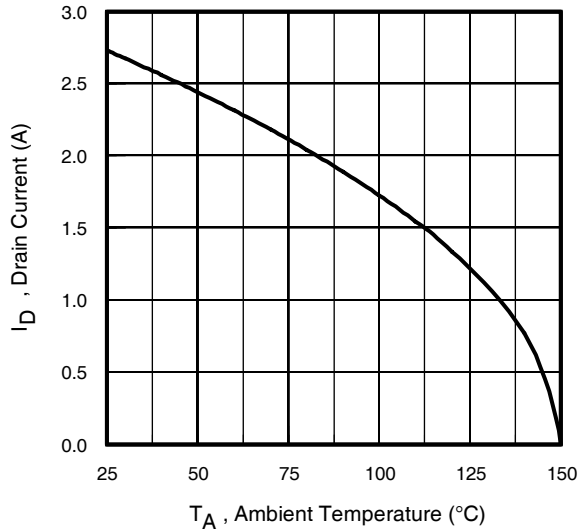


Fig 9. Maximum Drain Current Vs. Ambient Temperature

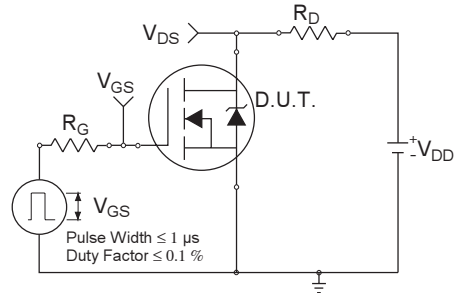


Fig 10a. Switching Time Test Circuit

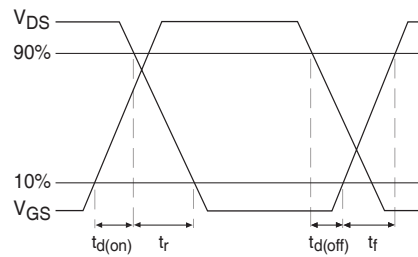


Fig 10b. Switching Time Waveforms

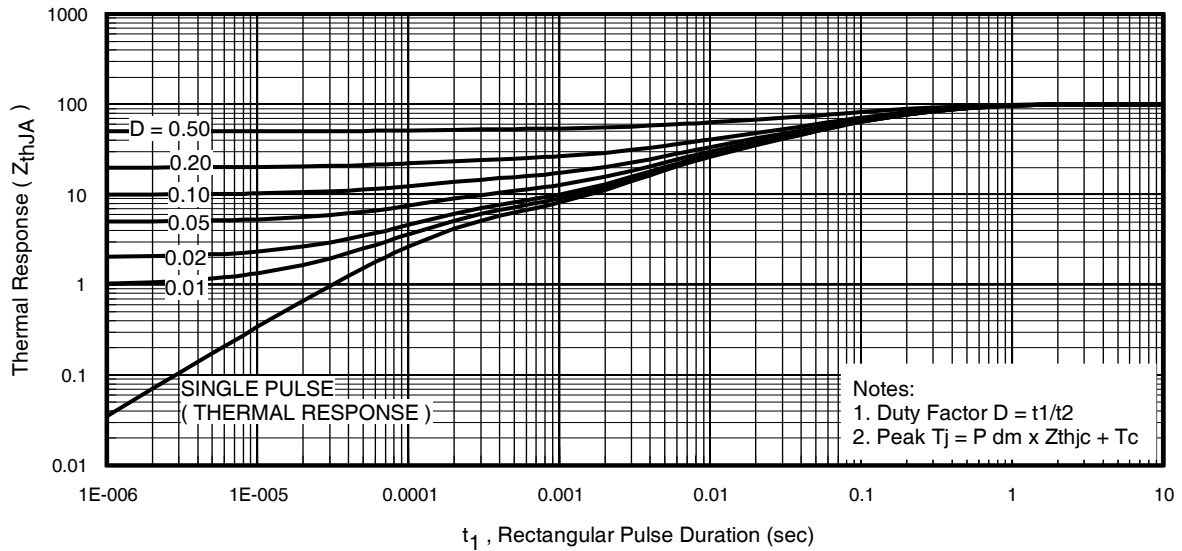
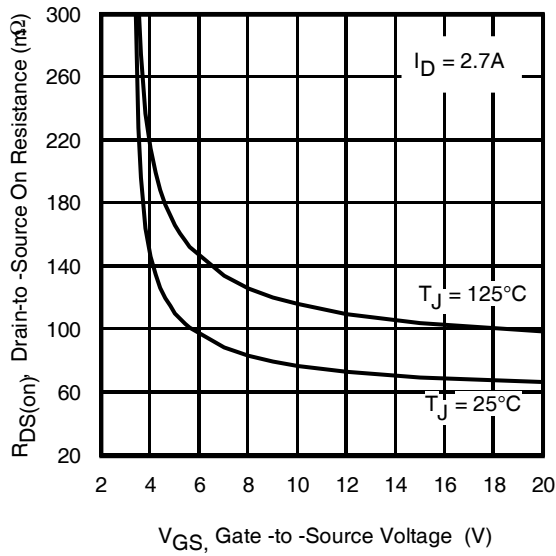
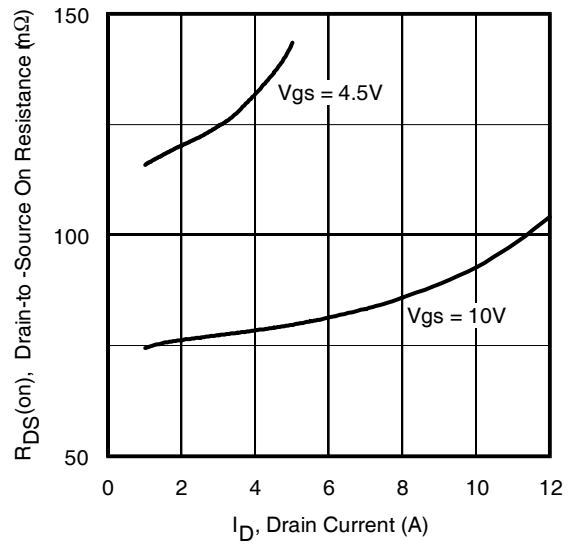


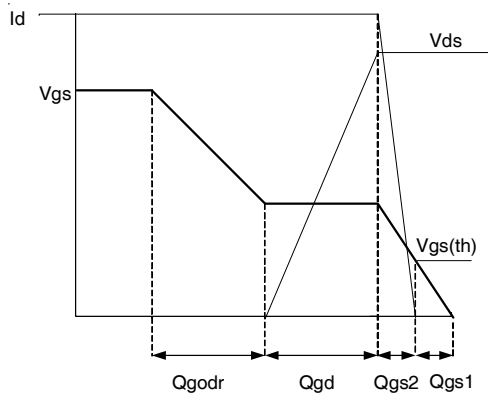
Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient



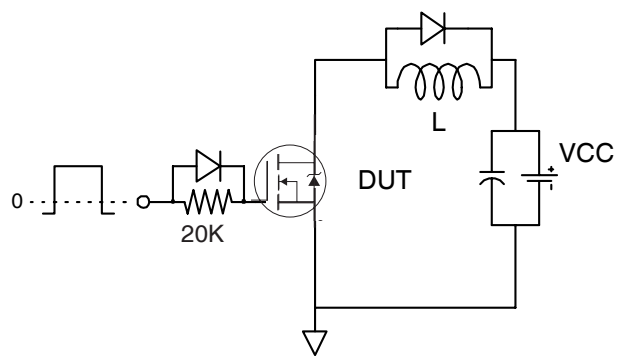
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



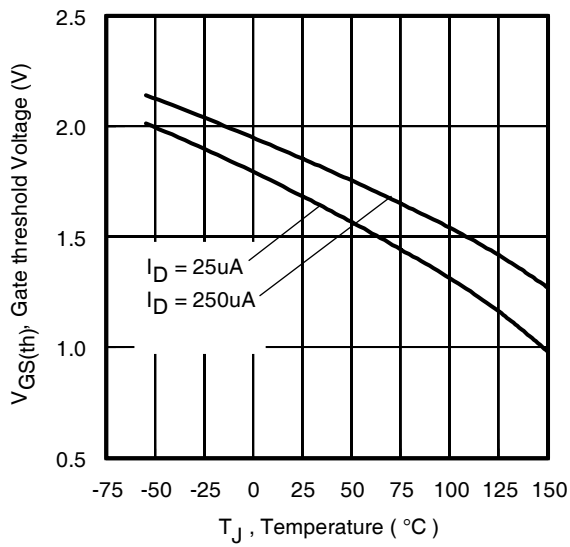
**Fig 13.** Typical On-Resistance Vs. Drain Current



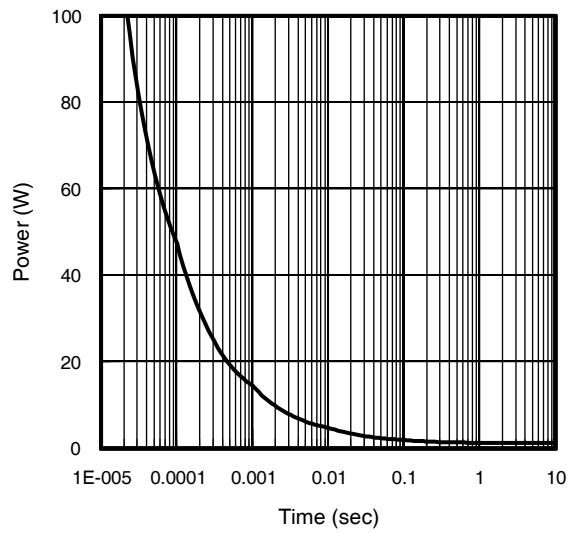
**Fig 14a.** Basic Gate Charge Waveform



**Fig 14b.** Gate Charge Test Circuit

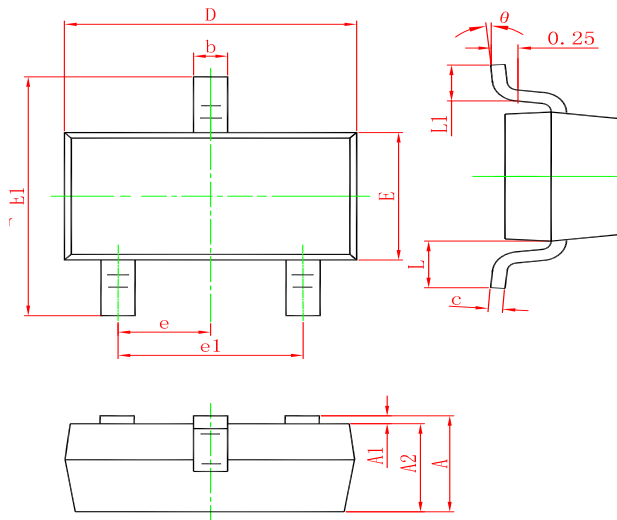


**Fig 15.** Typical Threshold Voltage Vs. Junction Temperature



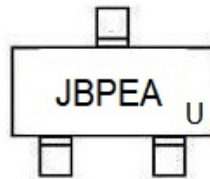
**Fig 16.** Typical Power Vs. Time

**SOT-23 PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Marking**



**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW IRLML2030TR	SOT-23	3000	Tape and reel



单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)